

Guowang Li

List of Publications by Year in descending order

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docs citations

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times ranked

1297
citing authors

#	ARTICLE	IF	CITATIONS
1	InAlN/AlN/GaN HEMTs With Regrown Ohmic Contacts and f_{T} of 370 GHz. IEEE Electron Device Letters, 2012, 33, 988-990.	3.9	292
2	Presence and origin of interface charges at atomic-layer deposited Al ₂ O ₃ /III-nitride heterojunctions. Applied Physics Letters, 2011, 99, .	3.3	140
3	MBE-Regrown Ohmics in InAlN HEMTs With a Regrowth Interface Resistance of 0.05 Ωcm^2 . IEEE Electron Device Letters, 2012, 33, 525-527.	3.9	118
4	210-GHz InAlN/GaN HEMTs With Dielectric-Free Passivation. IEEE Electron Device Letters, 2011, 32, 892-894.	3.9	88
5	Polarizationâ€œengineering in group IIIâ€œnitride heterostructures: New opportunities for device design. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1511-1516.	1.8	83
6	220-GHz Quaternary Barrier InAlGaN/AlN/GaN HEMTs. IEEE Electron Device Letters, 2011, 32, 1215-1217.	3.9	71
7	Ultrascaled InAlN/GaN High Electron Mobility Transistors with Cutoff Frequency of 400 GHz. Japanese Journal of Applied Physics, 2013, 52, 08JN14.	1.5	66
8	Quaternary Barrier InAlGaN HEMTs With f_{T}/f_{max} of 230/300 GHz. IEEE Electron Device Letters, 2013, 34, 378-380.	3.9	58
9	Polarization-Induced GaN-on-Insulator E/D Mode p-Channel Heterostructure FETs. IEEE Electron Device Letters, 2013, 34, 852-854.	3.9	55
10	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. Applied Physics Letters, 2017, 110, .	3.3	48
11	Threshold Voltage Control in $\text{Al}_{0.72}\text{Ga}_{0.28}\text{N}/\text{AlN}/\text{GaN}$ HEMTs by Work-Function Engineering. IEEE Electron Device Letters, 2010, 31, 954-956.	3.9	47
12	Quantum transport in graphene nanoribbons patterned by metal masks. Applied Physics Letters, 2010, 96, .	3.3	45
13	MBE growth of high conductivity single and multiple AlN/GaN heterojunctions. Journal of Crystal Growth, 2011, 323, 529-533.	1.5	45
14	Ultra-low resistance ohmic contacts to GaN with high Si doping concentrations grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	3.3	42
15	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. Applied Physics Letters, 2014, 104, .	3.3	42
16	Ultrathin Body GaN-on-Insulator Quantum Well FETs With Regrown Ohmic Contacts. IEEE Electron Device Letters, 2012, 33, 661-663.	3.9	40
17	InGaN Channel High-Electron-Mobility Transistors with InAlGaN Barrier and T_{max} of 260/220 GHz. Applied Physics Express, 2013, 6, 016503.	2.4	35
18	Metalâ€œface InAlN/AlN/GaN high electron mobility transistors with regrown ohmic contacts by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1617-1619.	1.8	25

#	ARTICLE	IF	CITATIONS
19	Subcritical barrier AlN/GaN E-Mode HFETs and inverters. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011, 208, 1620-1622.	1.8	16
20	High mobility two-dimensional electron gases in nitride heterostructures with high Al composition AlGa _{0.2} N alloy barriers. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	14
21	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and ¹⁵ N isotopes. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	13
22	Si-Containing Recessed Ohmic Contacts and 210 GHz Quaternary Barrier InAlGa _{0.2} N High-Electron-Mobility Transistors. <i>Applied Physics Express</i> , 2011, 4, 096502.	2.4	10
23	Ultra-thin Body GaN-on-insulator nFETs and pFETs: Towards III-nitride complementary logic. , 2012, , .		7
24	Time delay analysis in high speed gate-recessed E-mode InAlN HEMTs. <i>Solid-State Electronics</i> , 2013, 80, 67-71.	1.4	7
25	Barrier height, interface charge & tunneling effective mass in Al _{0.2} O ₃ /AlN/GaN HEMTs. , 2011, , .		3
26	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates. , 2015, , .		3
27	Effect of optical phonon scattering on the performance limits of ultrafast GaN transistors. , 2011, , .		2
28	Quantum transport in patterned graphene nanoribbons. , 2009, , .		1
29	High performance E-mode InAlN/GaN HEMTs: Interface states from subthreshold slopes. , 2010, , .		1
30	Comparative study of E- and D-mode InAlN/AlN/GaN HEMTs with f_T near 200 GHz. , 2011, , .		1
31	Work-function engineering in novel high Al composition Al _{0.72} Ga _{0.28} N/AlN/GaN HEMTs. , 2010, , .		0